

C. Page 24, please replace the last paragraph with the following paragraph.

-- Referring now to Fig. 20, partially reduced metal silicate layer **50** is converted to a silicate layer **52** by oxidation. Control of oxidation is critical during this step, as under-oxidation will result in decreased resistivity and over-oxidation may result in decreased capacitance for layer **52** (due to oxidation of the underlying silicon). Post-anneals in O₂ at about 400-550° for up to about 30 minutes generally increase capacitance while maintaining low leakage current. Anneals at higher temperatures or longer times tend to degrade capacitance. --

IN THE DRAWINGS

D. Please review the attached draft of new Fig. 21.